



MEMC 98-5751 (2358.4)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Mutti et al.

Serial No. 10/008,812

Filed November 13, 2001

For METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL TO
MINIMIZE GROWTH RATE AND DIAMETER DEVIATIONS

March 4, 2003

LETTER TO THE PATENT AND TRADEMARK OFFICE

TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

In response to the Office action mailed December 4, 2002, please consider the following remarks.

REMARKS

Applicants have thoroughly considered the Examiner's remarks but respectfully disagree and request further reconsideration of the application in light of the following clarifying remarks.

Claims 1 and 21 stand rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification. In particular, the Examiner asserts that "there is no teaching in the specification that the control loops are to act independently of the temperature." (Office action at page 2). Indeed, there is support in the specification for the claimed subject matter, and Applicants respectfully submit that the Examiner's determination is erroneous. For example, the application clearly states at page 13, lines 11-13 "[t]he present invention advantageously controls silicon crystal growth to minimize growth rate and diameter variations *independent of*